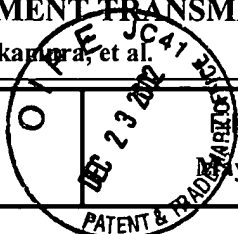


1765

AMENDMENT TRANSMITTAL LETTER (Large Entity)			Docket No. 1110/82822	
Applicant(s): Nakamura, et al.				
Serial No. 09/856,209	Filing Date May 18, 2001	Examiner Song, Matthew J.	Group Art Unit 1765	



Invention:

SILICON CRYSTAL AND PRODUCTION METHOD FOR SILICON SINGLE CRYSTAL WAFER

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

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Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

TC 1700

CLAIMS AS AMENDED

	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR	NUMBER EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE
TOTAL CLAIMS	-	20 =	0 x	\$18.00	\$0.00
INDEP. CLAIMS	-	3 =	0 x	\$84.00	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00

- ☒ No additional fee is required for amendment.
- ☐ Please charge Deposit Account No. _____ in the amount of _____
A duplicate copy of this sheet is enclosed.
- ☐ A check in the amount of _____ to cover the filing fee is enclosed.
- ☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 23-0920
A duplicate copy of this sheet is enclosed.
 - ☒ Any additional filing fees required under 37 C.F.R. 1.16.
 - ☒ Any patent application processing fees under 37 CFR 1.17.

G T Shekleton

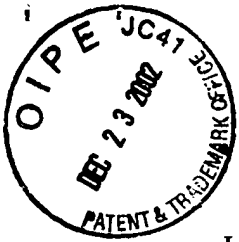
Signature

Dated: December 16, 2002

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I certify that this document and fee is being deposited December 16, 2002 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.	
<i>Gerald T. Shekleton</i>	
Signature of Person Mailing Correspondence	
Gerald T. Shekleton, Esq.	
Typed or Printed Name of Person Mailing Correspondence	



7C
12/31/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the U.S. Patent Application of:)
Applicant: Nakamura, et al.)
Serial No.: 09/856,209)
Filed: May 18, 2001)
For: SILICON CRYSTAL AND PRODUCTION)
METHOD FOR SILICON SINGLE)
CRYSTAL WAFER)

Attorney Docket:
1110/82822

Group Art Unit:
1765

AMENDMENT

Commissioner for Patents
"Attention: Box Amendment"
Washington, D.C. 20231

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TC 1700

Dear Sir:

The Office Action of October 15, 2002 has been carefully reviewed and the following amendments and remarks are made in response thereto.

IN THE CLAIMS

Please cancel[✓] claims 1, 2, 4-6, 11-12 without prejudice.

Please amend Claims 3, 8 and 10 as follows:

C' 3. (Amended) A silicon single crystal ingot production method wherein the silicon single crystal ingot production is performed by adjusting a distance between a silicon melt and a heat-shield member installed in a Czochralski-method silicon single crystal production equipment to change a temperature gradient within the crystal in a pulling axis direction.